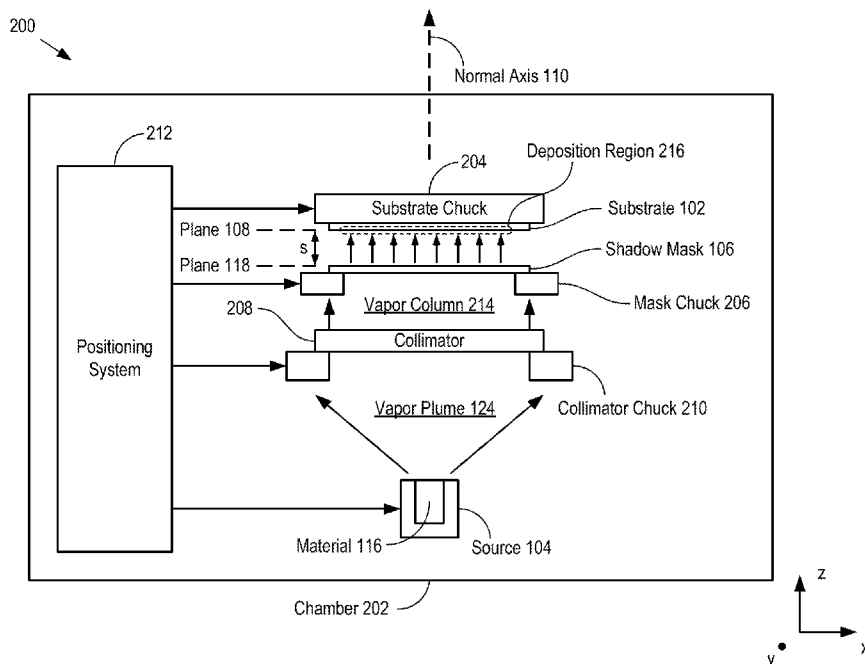




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FIG. 2



(57) Abstract: A direct-deposition system capable of forming a high-resolution pattern of material on a substrate is disclosed. Vaporized atoms from an evaporation source pass through an aperture pattern of a shadow mask to deposit on the substrate in the desired pattern. Prior to reaching the shadow mask, the vaporized atoms pass through a collimator that operates as a spatial filter that blocks any atoms not travelling along directions that are nearly normal to the substrate surface. As a result, the vaporized atoms that pass through the shadow mask exhibit little or no lateral spread (i.e., feathering) after passing through its apertures and the material deposits on the substrate in a pattern that has very high fidelity with the aperture pattern of the shadow mask. The present invention, therefore, mitigates the need for relatively large space between regions of deposited material normally required in the prior art, thereby enabling high-resolution patterning.



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DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN,  
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## **High-Precision Shadow-Mask-Deposition System and Method Therefor**

### **Statement of Related Cases**

[0001] This case claims priority to U.S. Provisional Patent Application Serial Number 62/340,793 filed on May 24, 2016 (Attorney Docket: 6494-208PR1), which is incorporated herein by reference.

### **Field of the Invention**

[0002] The present invention relates to thin-film deposition in general, and, more particularly, evaporation-based thin-film deposition.

### **Background of the Invention**

[0003] Shadow-mask-based deposition is a process by which a material is deposited onto the surface of a substrate such that the deposited material is patterned as desired during the deposition process itself. This is often referred to as "directly patterned" the patterned layer of material.

[0004] In a typical shadow-mask deposition process, the desired material is vaporized at a source that is located some distance from the substrate. As the vaporized atoms of the material travel toward the substrate, they must pass through a shadow mask that is positioned just in front of the substrate surface. The shadow mask contains openings (*i.e.*, apertures) whose arrangement matches that of the desired pattern for the material on the substrate (in similar fashion to a silk screen or art stencil). As a result, the vaporized atoms pass only through the apertures to deposit on the substrate surface.

[0005] Shadow-mask-based deposition has been used in the integrated-circuit (IC) industry to deposit patterns of material on substrates for many years, due, in part, to the fact that it avoids the need for patterning a material layer after it has been deposited. As a result, its use eliminates the need to expose the deposited material to harsh chemicals, such as acid-based etchants, caustic photolithography development chemicals, and the like, to pattern it. In addition, its use also reduces the amount of handling and additional processing to which the substrate must be subjected, thereby potentially reducing substrate breakage and increasing fabrication yield. For many materials, such as organic materials, patterning by shadow mask is virtually a necessity because the materials cannot be subjected to photolithographic chemicals.

[0006] Unfortunately, the feature resolution that can be obtained by shadow-mask deposition is diminished due to the fact that the deposited material tends to spread laterally after passing through the shadow mask – referred to as “feathering.” As a result, critical features must be separated by relatively large areas of open space between them. In many applications, this has limited the density of overall device resolution that can be obtained.

[0007] For example, active-matrix organic light-emitting-diode (AMOLED) displays require shadow-mask-based deposition of their light-emitting material because these materials cannot be subjected to photolithography or etching. For full-color AMOLED displays, each display pixel includes several regions – referred to as “sub-pixels” of light-emitting material, each emitting a different color. Due to feathering issues, however, relatively large safety-margin gaps must be included between these subpixel regions to ensure no overlap in deposited materials. In some cases, these gaps must be nearly as large as the subpixel itself which introduces undesired optical artifacts – particularly when viewed in near-to-eye applications, such as head mounted displays. Prior-art AMOLED displays, therefore, have typically been restricted to approximately 600 pixels-per-inch (ppi) or less which is insufficient for many applications, including near-to-eye augmented reality and virtual reality applications. In addition, the need for large gaps between subpixels gives rise to reduced pixel fill factor, which reduces display brightness. As a result, the current density through the organic layers must be increased to provide the desired brightness, which can decrease display lifetime.

[0008] An alternative approach is to use a shadow-mask with an aperture as large as the active area of the display itself to deposit a monochrome white-emitting organic layer across the entire display and then to pattern or deposit red, green and blue color filters on top of the OLED. These color filters absorb all of the emitted white light except for the red, green or blue portion of the spectrum (depending on the color filter), allowing a full color image to be created. However, these color filters absorb up to 80% of the emitted light which significantly reduces display brightness, again requiring operation at higher than desirable drive currents.

[0009] The need for a process that is suitable for directly patterning high-resolution patterns of material on a substrate remains unmet in the prior art.

### **Summary of the Invention**

[0010] The present invention enables high-resolution direct deposition of a patterned layer of material on a substrate. Embodiments of the present invention filter the propagation angles of vaporized atoms to a narrow range around a direction normal to the surface of the substrate. As a result, feathering of deposited material outside the lateral dimensions of features of a shadow mask is mitigated. Embodiments of the present invention are particularly well suited for use in deposition of sensitive materials, such as organic light-emitting material. Embodiments are also well suited for deposition of other thin- and thick-film layers in packaging applications, integrated-circuit processing applications, and the like.

[0011] An illustrative embodiment of the present invention is a direct-patterning deposition system in which a material is vaporized at a source such that it deposits on a surface of a substrate after passing through an aperture pattern of a shadow mask. Prior to their arrival at the shadow mask, the vaporized atoms pass through a collimator that blocks all vaporized atoms except those having propagation angles close to the direction normal to the substrate surface. As a result, the lateral deviation between the apertures and their respective regions of deposited material is reduced as compared to the prior art.

[0012] The collimator includes a plurality of channels having a high height-to-width aspect ratio, where the longitudinal axis of the channels is substantially aligned with the normal direction. As a result, those vaporized atoms travelling along directions other than close to normal are blocked by the inside walls of the channels.

[0013] In some embodiments, the source is dimensioned and arranged to provide a conically shaped vapor plume of vaporized atoms such that the entire substrate surface receives vaporized material at the same time. In some of these embodiments, the source is moved along a path such that the uniformity of the thickness of deposited material is improved over the two-dimensional area of the substrate surface.

[0014] In some embodiments, the source is a linear source that emits a fan-shaped vapor plume, where the linear source is moved along a direction that is unaligned with its longitudinal axis. In some of these embodiments, the source is moved along a direction that is substantially orthogonal to both the longitudinal axis of the source and the normal direction. In some of these embodiments, the source is moved along a non-linear path.

[0015] In some embodiments, the source includes a plurality of individual nozzles, each of which emits a conically shaped vapor plume such that the nozzles collectively provide a flow of vaporized atoms that is substantially uniform over the area of the substrate surface.

[0016] In some embodiments, the source is a two-dimensional planar source that is arranged parallel to and facing the substrate such that, when heated, organic material vaporizes uniformly across the planar surface of the source. In some embodiments, relative motion between the source and shadow mask is provided to improve the thickness uniformity of the deposited material over the two-dimensional area of the substrate surface.

[0017] An embodiment of the present invention is a system for depositing a first material on a plurality of deposition sites in a deposition region of a substrate, the plurality of deposition sites being arranged in a first arrangement, wherein the system comprises: a source for providing a first plurality of vaporized atoms of the first material, each vaporized atom of the first plurality thereof propagating along a propagation direction that is characterized by a propagation angle relative to a first direction that is normal to a first plane defined by the substrate, wherein the range of propagation angles of the first plurality of vaporized atoms spans a first angular range; a shadow mask comprising a plurality of apertures arranged in the first arrangement; and a collimator comprising a plurality of channels, the collimator being between the source and the shadow mask, wherein each channel of the plurality thereof is dimensioned and arranged to pass only vaporized atoms having a propagation angle within a second angular range that is smaller than the first angular range.

[0018] Another embodiment of the present invention is a system for depositing a first material on a plurality of deposition sites in a deposition region of a substrate, the plurality of deposition sites being arranged in a first arrangement, wherein the system comprises: a source that is operative for providing a plurality of vaporized atoms, each vaporized atom of the plurality thereof traveling along a propagation direction that defines a propagation angle, wherein the plurality of propagation angles span a first angular range; a shadow mask comprising a plurality of apertures arranged in the first arrangement, wherein the shadow mask and the plurality of deposition sites collectively define an acceptable angular range that is less than the first angular range; and a collimator that is located between the source and the shadow mask, the collimator comprising a plurality of channels,

each channel of the plurality thereof having a height-to-width aspect ratio that defines a filtered angular range that is less than or equal to the acceptable angular range.

[0019] Yet another embodiment of the present invention is a method for depositing a first material on a plurality of deposition sites arranged in a first arrangement on a substrate, wherein the method comprises: receiving a first plurality of vaporized atoms at a collimator that is located between a source and a shadow mask having a plurality of apertures arranged in the first arrangement, wherein the first plurality of vaporized atoms is characterized by a first range of propagation angles; selectively passing a second plurality of vaporized atoms through the collimator to the shadow mask, wherein the second plurality of vaporized atoms is characterized by a second range of propagation angles that is narrower than the first range of propagation angles; and enabling at least some of the second plurality of vaporized atoms to pass through the plurality of apertures to deposit on the substrate.

### **Brief Description of the Drawings**

[0020] FIG. 1 depicts a schematic drawing of a cross-section of the salient features of a direct-patterning deposition system in accordance with the prior art.

[0021] FIG. 2 depicts a schematic drawing of a cross-section of the salient features of a high-precision, direct-patterning deposition system in accordance with an illustrative embodiment of the present invention.

[0022] FIG. 3 depicts operations of a method for depositing a directly patterned layer of material on a substrate in accordance with the illustrative embodiment.

[0023] FIG. 4 depicts a schematic drawing of an enlarged view of a pixel region of substrate **102** and its corresponding aperture **120** of shadow mask **106**.

[0024] FIG. 5A depicts a schematic drawing of a cross-sectional view of a collimator in accordance with the illustrative embodiment.

[0025] FIGS. 5B-C depict schematic drawings of top and sectional views, respectively, of a region of collimator **208**.

### **Detailed Description**

[0026] FIG. 1 depicts a schematic drawing of a cross-section of the salient features of a direct-patterning deposition system in accordance with the prior art. System **100** is a

conventional evaporation system that deposits a desired pattern of material on a substrate by evaporating the material through a shadow mask positioned in front of the substrate. System **100** includes source **104** and shadow mask **106**, which are arranged within a low-pressure vacuum chamber (not shown).

[0027] Substrate **102** is a glass substrate suitable for the formation of active-matrix organic-light-emitting-diode (AMOLED) displays. Substrate **102** includes surface **114**, which defines plane **108** and normal axis **110**. Normal axis **110** is orthogonal to plane **108**. Surface **114** includes a plurality of deposition sites, **G**, for receiving material that emits green light, a plurality of deposition sites, **B**, for receiving material that emits blue light, and a plurality of deposition sites, **R**, for receiving material that emits red light. The deposition sites are arranged in a plurality of pixel regions **112** such that each pixel region includes one deposition site for the light-emitting material of each color.

[0028] Source **104** is a crucible for vaporizing material **116**, which is centered with respect to substrate **102** and material **116** is an organic light-emitting material that emits red light. When material **116** melts or sublimates within the low-pressure atmosphere of the vacuum chamber, source **104** ejects vaporized atoms **122** that propagate outward from the source in substantially ballistic fashion toward substrate **102**. The vaporized atoms ejected by source **104** collectively define vapor plume **124**.

[0029] Shadow mask **106** is a plate of structural material that includes apertures **120**. Shadow mask is substantially flat and defines plane **118**. The shadow mask is located between source **104** and substrate **102** such that it blocks the passage of all of the vaporized atoms except those that pass through its apertures. The shadow mask and substrate are separated by separation, **s**, (typically a few tens or hundreds of microns), planes **108** and **118** are substantially parallel, and apertures **120** are aligned with deposition sites **R**.

[0030] Ideally, when depositing red-emitting material **116**, vaporized atoms are incident only on deposition sites **R**. Unfortunately, vapor plume **124** includes vaporized atoms that travel along many different propagation directions **126**, many of which are not aligned with the direction of normal axis **110**. As a result, a large fraction of the vaporized atoms that pass through apertures **120** are travelling along propagation directions that have a significant lateral component. The point at which each vaporized atom is incident on surface **114** is geometrically determined by its propagation angle and the spatial



relationship between the substrate and shadow mask – specifically, spacing **s** and the alignment of apertures **120** with deposition sites **R**. For the purposes of this Specification, including the appended claims, the term “**propagation angle**” is defined as the angle formed by the propagation direction of a vaporized atom with respect to the direction normal to plane **108** of substrate **102** (*i.e.*, normal direction **128**, which is aligned with normal axis **110**). For example, vaporized atom **122** travels along a propagation direction **126**, which forms propagation angle,  $\theta_p$ , with respect to normal direction **128**.

[0031] The propagation angles of the vaporized atoms of vapor plume **124** span a relatively large angular range of  $-\theta_m$  to  $+\theta_m$ , which gives rise to significant disadvantages for prior-art direct-deposition systems. In particular, it results in the deposition of material **118** on surface **114** outside the perimeter of apertures **120**, which is typically referred to as “feathering.” Furthermore, the amount of feathering at an aperture increases with the distance of that aperture from the center of substrate **102**.

[0032] For apertures located near the center of vapor plume **124**, vaporized atoms **122** arriving at shadow mask **106** have propagation angles that are within a relatively small angular range. In other words, they are travelling along directions that are only slightly misaligned with normal axis **110**. As a result, vaporized atoms that pass through these apertures exhibit only minimal lateral drift (*i.e.*, feathering) after passing through the shadow mask. In this region, therefore, the lateral extent of the deposited material **116** is typically nearly aligned with the edges of apertures **120** (*i.e.*, it deposits primarily on the targeted deposition sites **R**).

[0033] For apertures further away from the center of vapor plume **124**, however, vaporized atoms arriving at shadow mask **106** span a relatively larger angular range and include propagation angles closer to  $|\theta_m|$ . As a result, in these regions, the lateral distance traveled by vaporized atoms after passing through the shadow mask is greater, leading to deposited material feathering out well beyond the lateral extent of the aperture. This results in a lateral offset,  $\delta f$ , between the edges of the aperture openings and the perimeters of the areas in which material **116** deposits. The deposited material, therefore, extends beyond the area of the targeted deposition sites. In some cases, such feathering can lead to deposition of material on adjacent deposition sites that are intended for different light-emitting material (*i.e.*, deposition sites, **B** and/or **G**), thereby leading to color mixing.

[0034] It should be noted that feathering is exacerbated by any additional misalignments between the shadow mask and substrate, such as deviations from the parallelism of planes **108** and **118** (*i.e.*, relative pitch and/or yaw between the mask and substrate), non-flatness of the shadow mask and/or substrate, and translational and/or rotational misalignment between the shadow mask and substrate. Still further, in many prior-art deposition systems (*e.g.*, systems for depositing more than one material, *etc.*), source **102** is located off-center from the substrate, which leads to even greater feathering problems.

[0035] It is an aspect of the present invention, however, that blocking vaporized atoms with propagation angles larger than desirable from reaching shadow mask **106** can significantly reduce feathering, thereby enabling patterns of deposited material having higher resolution and fidelity to the aperture pattern of the shadow mask.

[0036] FIG. 2 depicts a schematic drawing of a cross-section of the salient features of a high-precision, direct-patterning deposition system in accordance with an illustrative embodiment of the present invention. System **200** includes vacuum chamber **202**, substrate chuck **204**, source **104**, shadow mask **106**, mask chuck **206**, collimator **208**, and positioning system **210**. System **200** is operative for evaporating a desired pattern of material onto a substrate surface without the need for subsequent subtractive patterning operations, such as photolithography and etching.

[0037] System **200** is described herein with respect to the deposition of a pattern of light-emitting material on a glass substrate as part of the fabrication of an AMOLED display. However, it will be clear to one skilled in the art, after reading this Specification, that the present invention can be directed toward the formation of directly patterned layers of virtually any thin- and thick-film material (organic or inorganic) on any of a wide range of substrates, such as semiconductor substrates (*e.g.*, silicon, silicon carbide, germanium, *etc.*), ceramic substrates, metal substrates, plastic substrates, and the like. Further, although the illustrative embodiment is a thermal evaporation system, one skilled in the art will recognize, after reading this Specification, that the present invention can be directed toward virtually any material-deposition process, such as e-beam evaporation, sputtering, and the like. Still further, although the depicted example is a deposition system suitable for use in single-substrate planar processing, the present invention is also suitable for use in other fabrication approaches, such as cluster-tool processing, track processing, roll-to-roll processing, reel-to-reel processing, *etc.* As a result, the present invention is suitable for

use in myriad applications including, without limitation, packaging applications, IC fabrication, MEMS fabrication, nanotechnology device fabrication, ball-grid array (BGA) fabrication, and the like.

[0038] Vacuum chamber **202** is a conventional pressure vessel operative for providing a low-pressure atmosphere that supports evaporation of material **116**. It should be noted that vacuum chamber **202** can be a standalone unit, part of a cluster deposition system, or part of a track-deposition system where multiple evaporation chambers are arranged in linear chain. In some embodiments, vacuum chamber **202** includes several evaporation sources/shadow mask combinations that enable formation of different patterns of different materials, such as, for example, multiple light-emitting subpixels that emit light at different colors (*e.g.*, red, green, and blue).

[0039] FIG. 3 depicts operations of a method for depositing a directly patterned layer of material on a substrate in accordance with the illustrative embodiment. Method **300** is described herein with continuing reference to FIG. 2, as well as reference to FIGS. 4 and 5A-C. Method **300** begins with operation **301**, wherein collimator **208** is mounted in collimator chuck **210**.

[0040] Collimator **208** is a mechanically robust plate comprising a plurality of channels that are separated by thin walls, as described in more detail below and with respect to FIGS. 5A-C. Collimator **208** is dimensioned and arranged to function as a spatial filter that selectively passes vaporized atoms propagating along directions that are nearly normal to plane **108** (*i.e.*, that have very small propagation angles). Collimator **202**, therefore, mitigates feathering across the entirety of substrate **102**.

[0041] Collimator chuck **210** is an annular clamping mechanism for holding and locating the collimator relative to shadow mask **106**.

[0042] At operation **302**, shadow mask **106** is mounted in mask chuck **206**.

[0043] Mask chuck **206** is a mechanical clamp that locates shadow mask **106** between source **106** and substrate **116**. In some embodiments, mask chuck **206** is an electrostatic chuck that analogous to substrate chuck **204**. Typically, shadow mask **106** is supported only around its perimeter. As a result, shadow masks in the prior art tend to sag under gravitational forces. Such sag locally increases the gap between mask and substrate in the center and, therefore, exacerbates feathering in this region. In some embodiments, mask chuck **206** includes a slight curvature (*e.g.*, an upward slope) that biases the shadow

mask upward to counteract shadow-mask sag due to gravity. In some embodiments, a fine support structure may extend across the opening in mask chuck **206** to support the mask and reduce the gravitational sag.

[0044] At operation **303**, substrate **102** is mounted in substrate chuck **204**.

[0045] Substrate chuck **204** is a platen for securing substrate **102** such that the substrate is very flat. Substrate chuck **204** is dimensioned and arranged to contact substrate **102** only from one side (either the frontside or the backside) to mitigate interference with the deposition of material on the other side of the substrate. In the depicted example, substrate chuck **204** is an electrostatic chuck that applies a voltage across a dielectric to electrostatically "clamp" substrate **102** securely in place. In some embodiments, substrate chuck **204** secures the substrate via a different means, such as vacuum, mechanical clamps, from both sides of the substrate, *etc.* In some embodiments, substrate chuck **204** includes *in-situ* gap sensors that operate, with positioning system **212** to control the spacing and degree of parallelism between substrate **102** and shadow mask **106**.

[0046] At operation **304**, the relative positions of substrate **102**, shadow mask **106**, and collimator **208** are controlled by positioning system **212**.

[0047] Positioning system **212** is a system for controlling the relative positions of substrate **102**, source **104**, shadow mask **106**, and collimator **208**. The positioning system includes three six-axis manipulators and an optical alignment system to control the alignment between substrate **102** and shadow mask **106**. Each of the six-axis manipulators is operatively connected with each of substrate chuck **204**, mask chuck **206**, and collimator chuck **210** to control its position along and rotation about each of the x-, y-, and z-axes. In some embodiments, the position of at least one of mask chuck **206** and collimator chuck **210** is not controlled by a six-axis positioner. In some embodiments, positioning system **212** also includes a rotation stage for controlling the relative rotational alignment of substrate **102** and shadow mask **106**.

[0048] In operation **304**, positioning system **212** locates the substrate and shadow mask such that deposition sites, **R**, in deposition region **216** are aligned with apertures **120**, planes **108** and **118** are parallel and the separation, **s**, between the substrate and shadow mask is as close to zero (*i.e.*, in contact) as possible – preferably within a few

microns (e.g., 1-5 microns). In some embodiments, **s** is another suitable separation distance.

[0049] At operation **305**, source **104** generates vapor plume **124**. As described above and with respect to FIG. 1, the propagation angles of the vaporized atoms of vapor plume **124** span a relatively large angular range of  $-\theta m$  to  $+\theta m$ .

[0050] As discussed above and with respect to FIG. 1, the lateral and rotation alignments between substrate **102** and shadow mask **106**, the separation, **s**, between them, and the range of propagation angles,  $\theta p$ , of the vaporized atoms incident on the shadow mask determines the amount of feathering that occurs at surface **114** of the substrate.

[0051] FIG. 4 depicts a schematic drawing of an enlarged view of a pixel region of substrate **102** and its corresponding aperture **120** of shadow mask **106**. As shown in the figure, for perfect fidelity between aperture **120** and the deposition of material on deposition site, **R**, the propagation angles of vaporized atoms passed by shadow mask **106** must be within the acceptable range of  $-\theta a$  to  $+\theta a$ . For the purposes of this Specification, including the appended claims, the term "acceptable angular range" is defined as the range of propagation angles that is desired to be passed by the shadow mask, which spans the angular range from  $-\theta a$  to  $+\theta a$ . Typically, the acceptable angular range is that range of angles that enables material **116** to deposit only on deposition sites **R** after passing through apertures **120**. In some embodiments, the acceptable angular range includes a small guard band around the deposition sites to allow for feathering that is less than half the spacing between the closest deposition sites. Any vaporized atom incident on the shadow mask having a propagation angle outside this range would deposit on surface **114** beyond the lateral extent of deposition site **R**.

[0052] At operation **306**, vapor plume **124** is filtered by collimator **208** to give rise to vapor column **214**.

[0053] FIG. 5A depicts a schematic drawing of a cross-sectional view of a collimator in accordance with the illustrative embodiment. Collimator **208** includes body **502**, which is patterned to form a plurality of channels **504**, each of which extends through the thickness of body **502**.

[0054] Body **502** is a glass plate suitable for planar processing. In the depicted example, body **502** has a thickness of approximately 25 millimeters (mm); however, any

practical thickness can be used without departing from the scope of the present invention. In some embodiments, body **502** comprises a different structurally rigid material that is suitable for withstanding the temperatures associated with thermal and/or e-beam evaporation without significant deformation. Materials suitable for use in body **502** include, without limitation, semiconductors (*e.g.*, silicon, silicon-carbide, *etc.*), ceramics (*e.g.*, alumina, *etc.*), composite materials (*e.g.*, carbon fibers, *etc.*), fiber glass, printed circuit board, metals, polymers (*e.g.*, polyetheretherketone (PEEK), *etc.*), and the like.

[0055] Channels **504** are through-holes formed in body **502** using a conventional processing operation, such as metal forming, drilling, electron-discharge machining, deep reactive-ion etching (DRIE), and the like. In the depicted example, channels **504** have a circular cross-section with a diameter of approximately 3 mm. Channels **504**, therefore, have a height-to-width aspect ratio of approximately 8:1. Preferably, the height-to-width aspect ratio is at least equal to 3:1. In addition, for height-to-width aspect ratios that exceed 100:1, the flow of vaporized atoms through the collimator begins to diminish to undesirable levels; however, height-to-width aspect ratios in excess of 100:1 are within the scope of the present invention. In some embodiments, channels **504** have a cross-sectional shape other than circular (*e.g.*, square, rectangular, hexagonal, octagonal, irregular, *etc.*).

[0056] The formation of channels **504** give rise to a plurality of walls **506**, which reside between the channels. Preferably, to enable high throughput, walls **506** are as thin as possible without sacrificing the structural integrity of body **502**. In the depicted example, walls **506** have an average thickness of approximately **500** microns; however, any practical thickness can be used for walls **506**.

[0057] FIGS. 5B-C depict schematic drawings of top and sectional views, respectively, of a region of collimator **208**. Channels **506** are arranged in a honeycomb arrangement wherein columns are periodic and adjacent columns are offset from their neighbors by a half period. In some embodiments, the channels are arranged in a different arrangement, such as two-dimensional periodic, hexagonally close-packed, random, and the like.

[0058] As depicted in FIG. 5C, the aspect ratio of channel **504** defines a filtered angular range. For the purposes of this Specification, including the appended claims, the term “**filtered angular range**” is defined as the range of propagation angles that will pass through collimator **208**, which spans the angular range from  $-\theta_c$  to  $+\theta_c$ . As a result, a

vaporized atom having a propagation angle larger than  $|\theta_c|$  will be blocked by the collimator.

[0059] One skilled in the art will recognize that the dimensions provided above for body **502**, channels **504**, and walls **506** are merely exemplary and that other dimensions can be used without departing from the scope of the present invention.

[0060] At operation **307**, apertures **120** pass vaporized atoms of vapor column **214** such that they deposit on deposition sites **R** in deposition region **216**.

[0061] At optional operation **308**, positioning system **212** imparts motion on collimator **208** to improve the uniformity of vaporized-atom density across the lateral extent of vapor column **214**, thereby improving the deposition uniformity across the deposition sites on substrate **102**. In some embodiments, positioning system **212** is operative for imparting an oscillating motion to collimator **208**.

[0062] It should be noted that, in the illustrative embodiment, source **104** is substantially a point source for material **116** because the open area of its crucible is significantly smaller than the area of substrate **102**.

[0063] At optional operation **309**, positioning system **212** moves source **102** in the x-y plane, relative to the substrate, to improve deposition uniformity.

[0064] In some embodiments, source **104** is a linear evaporation source that comprises a plurality of nozzles that emits a fan-shaped vapor plume of vaporized atoms. In some embodiments, positioning system **212** moves the linear source along a direction that is unaligned with its longitudinal axis in the x-y plane to improve the uniformity of the deposited material on substrate **102**. In some embodiments, this path is a line that is substantially orthogonal to both the linear arrangement of nozzles and normal axis **110**. In some of embodiments, the linear source is moved along a non-linear path in the x-y plane.

[0065] In some embodiments, source **104** includes a two-dimensional arrangement of nozzles, each of which emits a conically shaped vapor plume such that the plurality of nozzles collectively provides a flow of vaporized atoms that is substantially uniform over the area of the substrate surface. In some embodiments, positioning system **212** moves the two-dimensional arrangement of nozzles to facilitate deposition uniformity. In some embodiments, the two-dimensional arrangement of nozzles is rotated in-plane to facilitate deposition uniformity.

[0066] In some embodiments, source **104** is a two-dimensional planar source that includes a layer of material **116** distributed across its top surface. The source is arranged such that this top surface is parallel to and facing substrate **102**. When heated, material **116** vaporizes uniformly across the plane. Exemplary planar evaporation sources suitable for use in embodiments of the present invention are disclosed by Tung, *et al.*, in "OLED Fabrication by Using a Novel Planar Evaporation Technique," *Int. J. of Photoenergy*, Vol. 2014(18), pp. 1-8 (2014), which is incorporated herein by reference.

[0067] In some embodiments, to improve the uniformity with which material **116** deposits over the two-dimensional area of surface **114**, positioning system **212** imparts a relative motion between source **104** and the combination of substrate **102** and shadow mask **106** by moving at least one of the substrate/mask combination and the source.

[0068] It is to be understood that the disclosure teaches just some embodiments in accordance with the present invention and that many variations of the invention can easily be devised by those skilled in the art after reading this disclosure and that the scope of the present invention is to be determined by the following claims.



What is claimed is:

**1.** A system for depositing a first material on a plurality of deposition sites in a deposition region of a substrate, the plurality of deposition sites being arranged in a first arrangement, wherein the system comprises:

a source for providing a first plurality of vaporized atoms of the first material, each vaporized atom of the first plurality thereof propagating along a propagation direction that is characterized by a propagation angle relative to a first direction that is normal to a first plane defined by the substrate, wherein the range of propagation angles of the first plurality of vaporized atoms spans a first angular range;

a shadow mask comprising a plurality of apertures arranged in the first arrangement; and

a collimator comprising a plurality of channels, the collimator being between the source and the shadow mask, wherein each channel of the plurality thereof is dimensioned and arranged to pass only vaporized atoms having a propagation angle within a second angular range that is smaller than the first angular range.

**2.** The system of claim 1 wherein the first material is an organic material.

**3.** The system of claim 2 wherein the first material is an organic material operative for emitting light.

**4.** The system of claim 1 wherein the plurality of deposition sites and the plurality of apertures collectively define an acceptable angular range, and wherein the second angular range is less than or equal to the acceptable angular range.

**5.** The system of claim 1 wherein each of the plurality of channels is characterized by a height-to-width aspect ratio that is equal to or greater than approximately 3:1.

**6.** The system of claim 1 wherein each of the plurality of channels is characterized by a height-to-width aspect ratio that is equal to or greater than 8:1.

**7.** The system of claim 1 wherein the deposition region has a first length along a second direction that is orthogonal to the first direction, and wherein the source includes a plurality of nozzles for emitting the plurality of vaporized atoms, the plurality of nozzles being arranged in a second arrangement having a second length along the second direction, the second length being greater than or equal to the first length.

**8.** The system of claim 7 wherein the source is movable relative to the deposition region along a third direction, the first direction, second direction, and third direction being mutually orthogonal.

**9.** The system of claim 7 wherein the second arrangement is a two-dimensional arrangement that has a third length along a third direction, the first direction, second direction, and third direction being mutually orthogonal.

**10.** The system of claim 1 wherein the source has a single nozzle for emitting the plurality of vaporized atoms, the source being movable relative to the deposition region in two dimensions within a second plane that is substantially parallel with the first plane.

**11.** The system of claim 1 further comprising a positioning system that is operative for imparting a relative motion between the substrate and the collimator.

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**12.** A system for depositing a first material on a plurality of deposition sites in a deposition region of a substrate, the plurality of deposition sites being arranged in a first arrangement, wherein the system comprises:

a source that is operative for providing a plurality of vaporized atoms, each vaporized atom of the plurality thereof traveling along a propagation direction that defines a propagation angle, wherein the plurality of propagation angles span a first angular range;

a shadow mask comprising a plurality of apertures arranged in the first arrangement, wherein the shadow mask and the plurality of deposition sites collectively define an acceptable angular range that is less than the first angular range; and

a collimator that is located between the source and the shadow mask, the collimator comprising a plurality of channels, each channel of the plurality thereof having a height-to-width aspect ratio that defines a filtered angular range that is less than or equal to the acceptable angular range.

**13.** The system of claim 12 wherein the substrate defines a first plane and a first direction that is normal to the first plane, and wherein the source comprises a plurality of nozzles for emitting the plurality of vaporized atoms, the plurality of nozzles being arranged in a second arrangement that has a first length along a second direction in a second plane that is substantially parallel with the first plane, and further wherein the source is movable along a path in the second plane, the path being unaligned with the second direction.

**14.** The system of claim 12 wherein the deposition region has a first area in the first plane, and wherein the source includes a first nozzle for emitting the plurality of vaporized atoms, and further wherein the source is movable within a second plane that is substantially parallel with the first plane.

**15.** The system of claim 12 further comprising a positioning system, the positioning system being operative for imparting a relative motion between the collimator and the substrate.

**16.** The system of claim 11 wherein height-to-width aspect ratio is at least 3:1.

**17.** The system of claim 11 wherein height-to-width aspect ratio is at least 8:1.

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**18.** A method for depositing a first material on a plurality of deposition sites arranged in a first arrangement on a substrate, wherein the method comprises:

receiving a first plurality of vaporized atoms at a collimator that is located between a source and a shadow mask having a plurality of apertures arranged in the first arrangement, wherein the first plurality of vaporized atoms is characterized by a first range of propagation angles;

selectively passing a second plurality of vaporized atoms through the collimator to the shadow mask, wherein the second plurality of vaporized atoms is characterized by a second range of propagation angles that is narrower than the first range of propagation angles; and

enabling at least some of the second plurality of vaporized atoms to pass through the plurality of apertures to deposit on the substrate.

**19.** The method of claim 18 further comprising providing the collimator such that it includes a plurality of channels, each channel of the plurality thereof having a height-to-width aspect ratio that determines the second range of propagation angles.

**20.** The method of claim 19 wherein the height-to-width aspect ratio is based on an acceptable angular range, the acceptable angular range being defined by the substrate and the shadow mask.

**21.** The method of claim 20 wherein the height-to-width aspect ratio defines a filtered angular range that is less than or equal to the acceptable angular range.

**22.** The method of claim 18 further comprising:

generating the first plurality of vaporized atoms at a source; and moving the source relative to the substrate.

**23.** The method of claim 22 further comprising providing the source as a linear arrangement of nozzles.

**24.** The method of claim 22 further comprising providing the source as a two-dimensional arrangement of nozzles.

**25.** The method of claim 18 further comprising imparting a relative motion between the collimator and the substrate.

## AMENDED CLAIMS

received by the International Bureau on 24 August 2017 (24.08.2017)

What is claimed is:

**1.** A system for depositing a first material on a plurality of deposition sites in a deposition region of a substrate, the plurality of deposition sites being arranged in a first arrangement, wherein the system comprises:

a source for providing a first plurality of vaporized atoms of the first material, each vaporized atom of the first plurality thereof propagating along a propagation direction that is characterized by a propagation angle relative to a first direction that is normal to a first plane defined by the substrate, wherein the range of propagation angles of the first plurality of vaporized atoms spans a first angular range;

a shadow mask comprising a plurality of apertures arranged in the first arrangement; and

a collimator comprising a plurality of channels, the collimator being between the source and the shadow mask, wherein each channel of the plurality thereof is dimensioned and arranged to pass only vaporized atoms having a propagation angle within a second angular range that is smaller than the first angular range.

**2.** The system of claim 1 wherein the first material is an organic material.

**3.** The system of claim 2 wherein the first material is an organic material operative for emitting light.

**4.** The system of claim 1 wherein the plurality of deposition sites and the plurality of apertures collectively define an acceptable angular range, and wherein the second angular range is less than or equal to the acceptable angular range.

**5.** The system of claim 1 wherein each of the plurality of channels is characterized by a height-to-width aspect ratio that is equal to or greater than approximately 3:1.

**6.** The system of claim 1 wherein each of the plurality of channels is characterized by a height-to-width aspect ratio that is equal to or greater than 8:1.

**7.** The system of claim 1 wherein the deposition region has a first length along a second direction that is orthogonal to the first direction, and wherein the source includes a plurality of nozzles for emitting the plurality of vaporized atoms, the plurality of nozzles being arranged in a second arrangement having a second length along the second direction, the second length being greater than or equal to the first length.

**8.** The system of claim 7 wherein the source is movable relative to the deposition region along a third direction, the first direction, second direction, and third direction being mutually orthogonal.

**9.** The system of claim 7 wherein the second arrangement is a two-dimensional arrangement that has a third length along a third direction, the first direction, second direction, and third direction being mutually orthogonal.

**10.** The system of claim 1 wherein the source has a single nozzle for emitting the plurality of vaporized atoms, the source being movable relative to the deposition region in two dimensions within a second plane that is substantially parallel with the first plane.

**11.** The system of claim 1 further comprising a positioning system that is operative for imparting a relative motion between the substrate and the collimator.

**12.** A system for depositing a first material on a plurality of deposition sites in a deposition region of a substrate, the plurality of deposition sites being arranged in a first arrangement, wherein the system comprises:

a source that is operative for providing a plurality of vaporized atoms, each vaporized atom of the plurality thereof traveling along a propagation direction that defines a propagation angle, wherein the plurality of propagation angles span a first angular range;

a shadow mask comprising a plurality of apertures arranged in the first arrangement, wherein the shadow mask and the plurality of deposition sites collectively define an acceptable angular range that is less than the first angular range; and

a collimator that is located between the source and the shadow mask, the collimator comprising a plurality of channels, each channel of the plurality thereof having a height-to-width aspect ratio that defines a filtered angular range that is less than or equal to the acceptable angular range.

**13.** The system of claim 12 wherein the substrate defines a first plane and a first direction that is normal to the first plane, and wherein the source comprises a plurality of nozzles for emitting the plurality of vaporized atoms, the plurality of nozzles being arranged in a second arrangement that has a first length along a second direction in a second plane that is substantially parallel with the first plane, and further wherein the source is movable along a path in the second plane, the path being unaligned with the second direction.

**14.** The system of claim 12 wherein the deposition region has a first area in the first plane, and wherein the source includes a first nozzle for emitting the plurality of vaporized atoms, and further wherein the source is movable within a second plane that is substantially parallel with the first plane.

**15.** The system of claim 12 further comprising a positioning system, the positioning system being operative for imparting a relative motion between the collimator and the substrate.

**16.** The system of claim 11 wherein height-to-width aspect ratio is at least 3:1.

**17.** The system of claim 11 wherein height-to-width aspect ratio is at least 8:1.

**18.** A method for depositing a first material on a plurality of deposition sites arranged in a first arrangement on a substrate, wherein the method comprises:

receiving a first plurality of vaporized atoms at a collimator that is located between a source and a shadow mask having a plurality of apertures arranged in the first arrangement, wherein the first plurality of vaporized atoms is characterized by a first range of propagation angles;

selectively passing a second plurality of vaporized atoms through the collimator to the shadow mask, wherein the second plurality of vaporized atoms is characterized by a second range of propagation angles that is narrower than the first range of propagation angles; and

enabling at least some of the second plurality of vaporized atoms to pass through the plurality of apertures to deposit on the substrate.

**19.** The method of claim 18 further comprising providing the collimator such that it includes a plurality of channels, each channel of the plurality thereof having a height-to-width aspect ratio that determines the second range of propagation angles.

**20.** The method of claim 19 wherein the height-to-width aspect ratio is based on an acceptable angular range, the acceptable angular range being defined by the substrate and the shadow mask.

**21.** The method of claim 20 wherein the height-to-width aspect ratio defines a filtered angular range that is less than or equal to the acceptable angular range.

**22.** The method of claim 18 further comprising:  
generating the first plurality of vaporized atoms at a source; and  
moving the source relative to the substrate.

**23.** The method of claim 22 further comprising providing the source as a linear arrangement of nozzles.

**24.** The method of claim 22 further comprising providing the source as a two-dimensional arrangement of nozzles.

**25.** The method of claim 18 further comprising imparting a relative motion between the collimator and the substrate.

**26.** The system of claim 1 further comprising a mask chuck for holding the shadow mask around its perimeter, the mask chuck being dimensioned and arranged to mitigate gravity-induced sag of the shadow mask.

**27.** The system of claim 26 wherein the mask chuck is dimensioned and arranged to induce a mechanical bias in the shadow mask for mitigating the gravity-induced sag.

**28.** The system of claim 27 wherein the mask chuck is characterized by a slope that gives rise to the mechanical bias when the shadow mask is mounted in the mask chuck.

**29.** The system of claim 26 further comprising a support structure located in an opening of the mask chuck, wherein the support structure supports the shadow mask when the shadow mask is mounted in the mask chuck.

**30.** The system of claim 12 further comprising a mask chuck for holding the shadow mask around its perimeter, the mask chuck being dimensioned and arranged to mitigate gravity-induced sag of the shadow mask.

**31.** The system of claim 30 wherein the mask chuck is dimensioned and arranged to induce a mechanical bias in the shadow mask for mitigating the gravity-induced sag.

**32.** The system of claim 31 wherein the mask chuck is characterized by a slope that gives rise to the mechanical bias when the shadow mask is mounted in the mask chuck.

**33.** The system of claim 30 further comprising a support structure located in an opening of the mask chuck, wherein the support structure supports the shadow mask when the shadow mask is mounted in the mask chuck.

**34.** The method of claim 18 further comprising mounting the shadow mask in a mask chuck operative for mitigating gravity-induced sag of the shadow mask.

**35.** The method of claim 34 further comprising providing the mask chuck such that it induces a mechanical bias in the shadow mask that mitigates the gravity-induced sag.

**36.** The method of claim 35 wherein the mask chuck is provided such that it is characterized by a slope that gives rise to the mechanical bias when the shadow mask is mounted in the mask chuck.

**37.** The method of claim 34 further comprising providing the mask chuck such that it includes a support structure located in an opening of the mask chuck, wherein the support structure supports the shadow mask when the shadow mask is mounted in the mask chuck.



FIG. 1 (Prior Art)

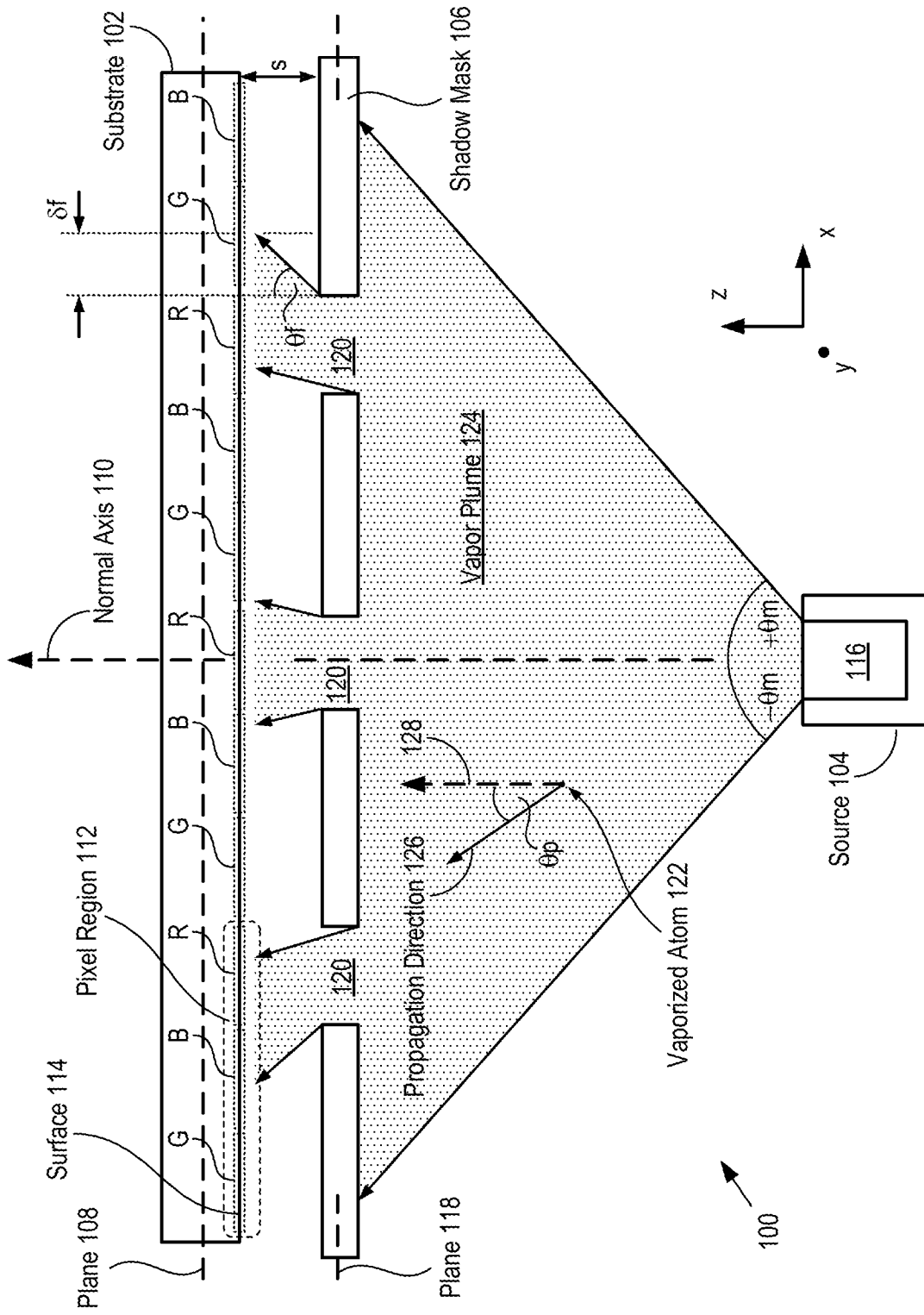


FIG. 2

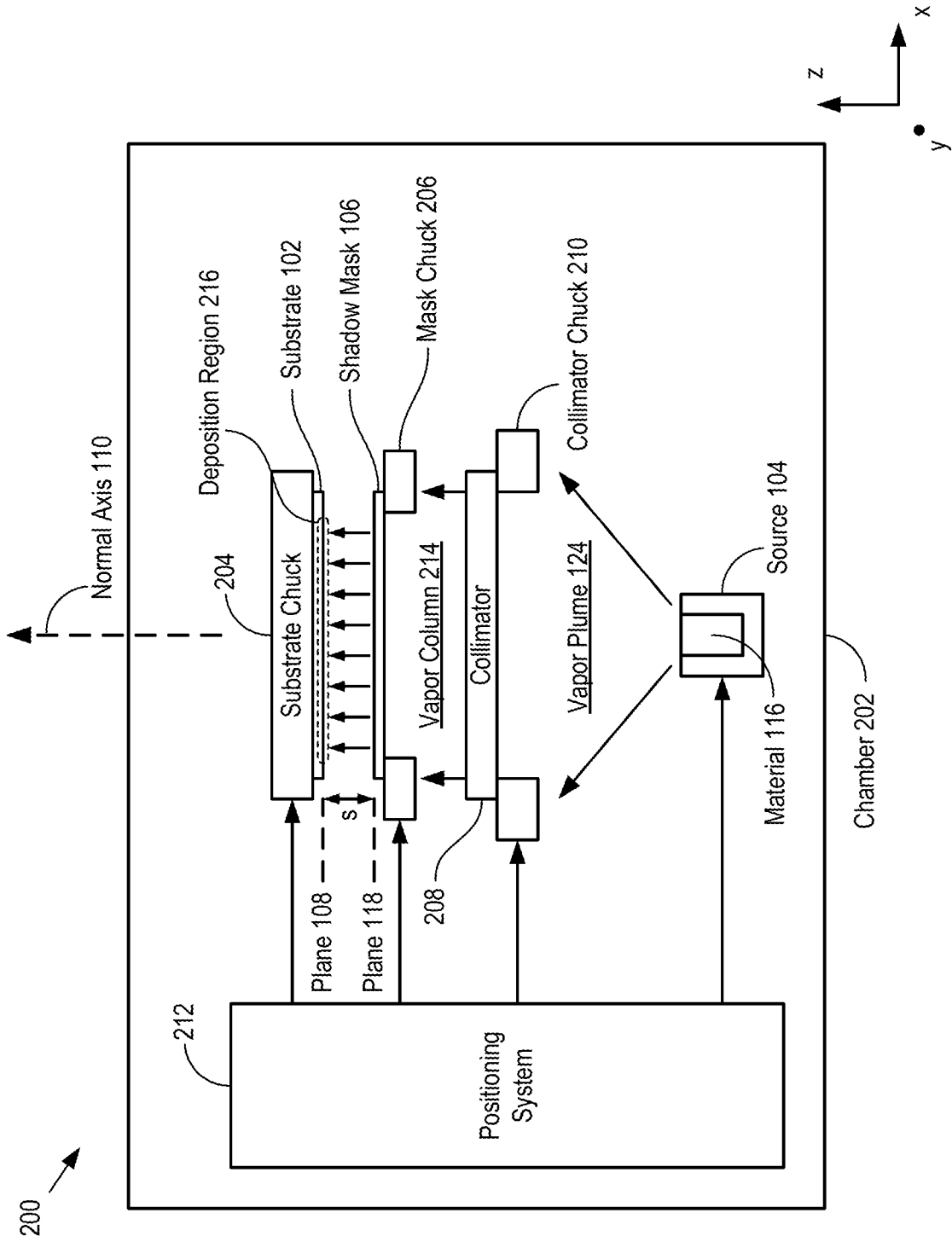


FIG. 3

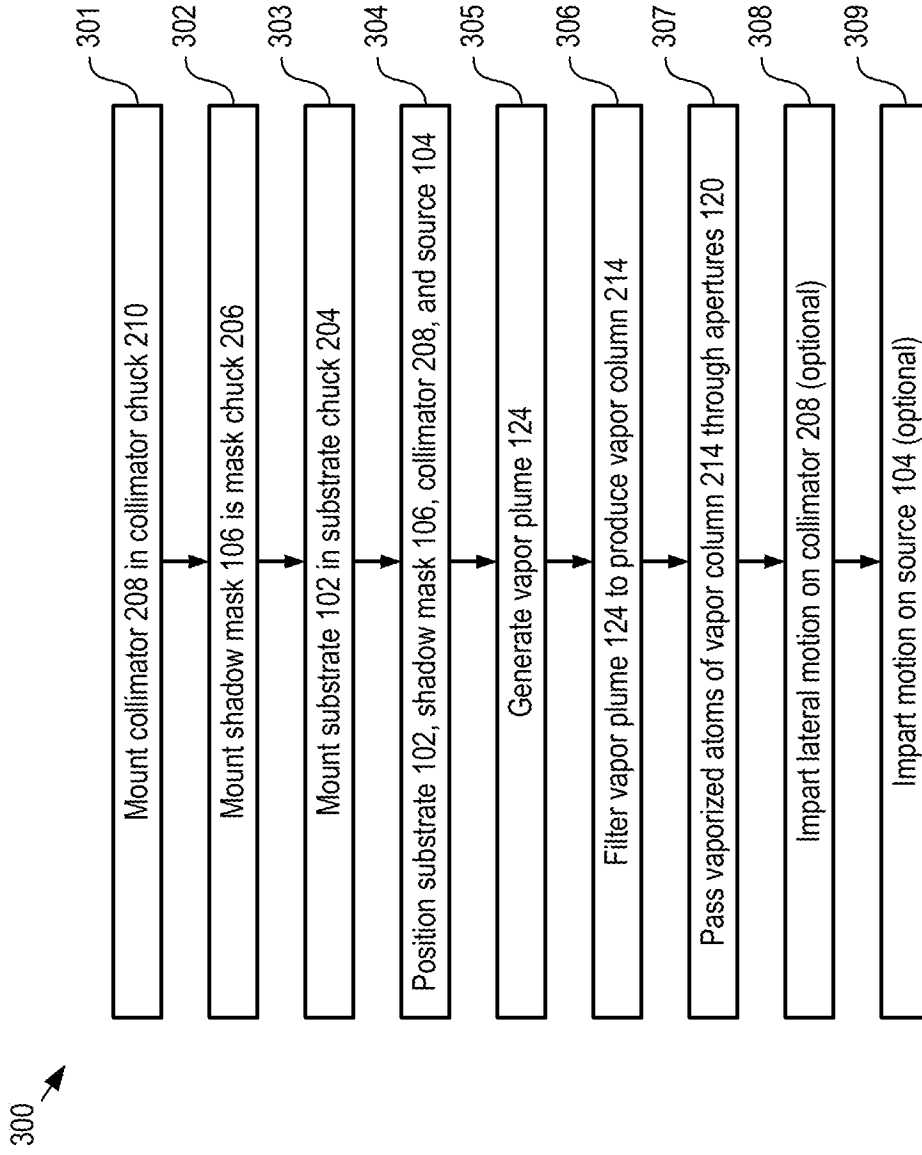
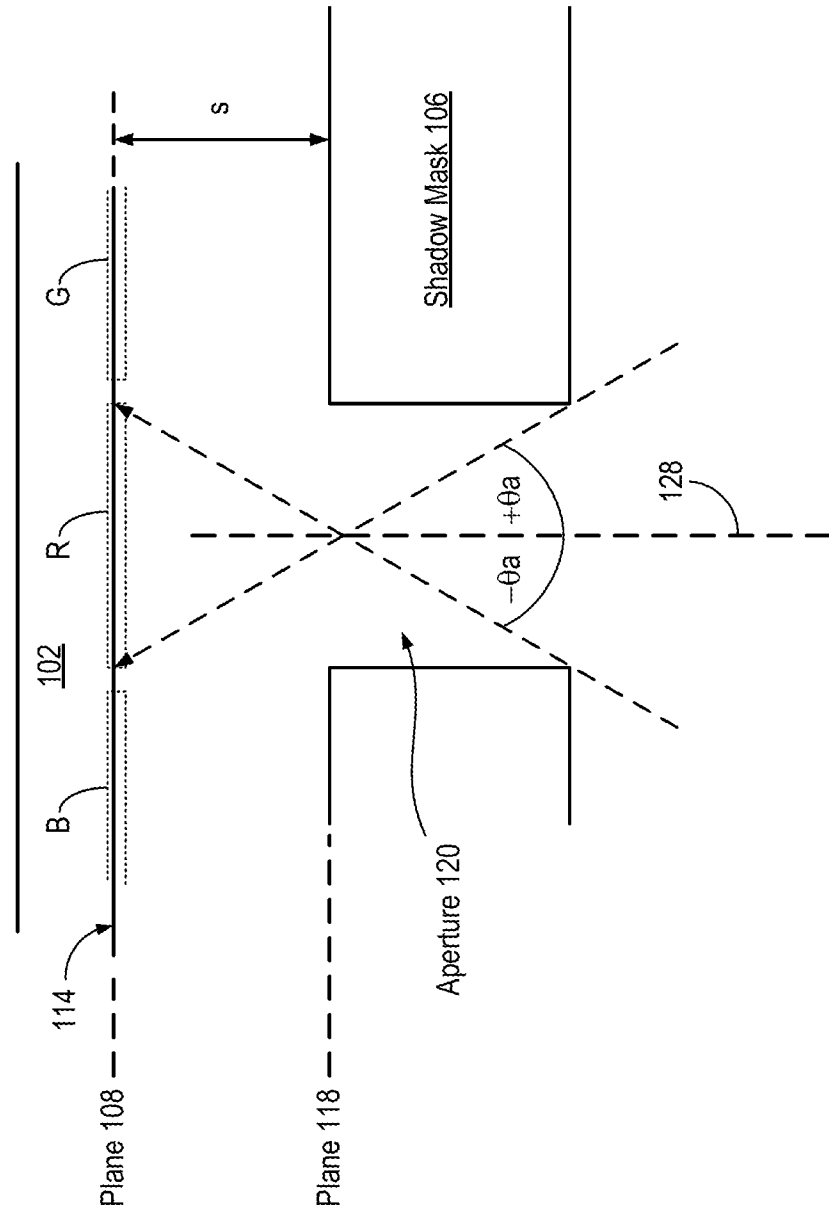
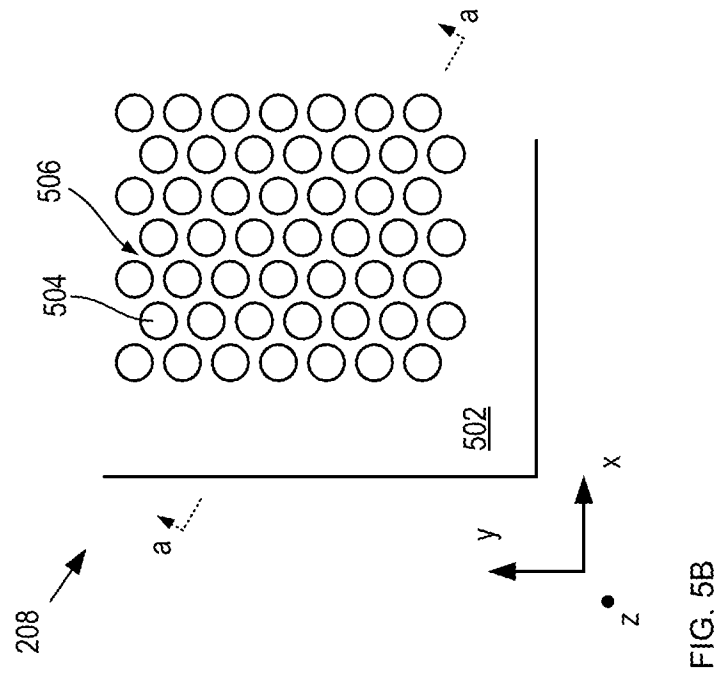
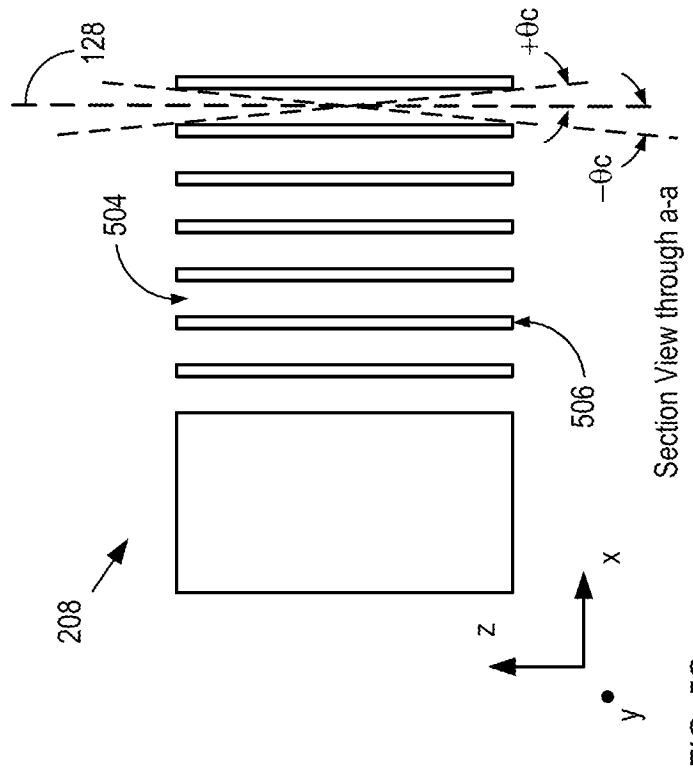
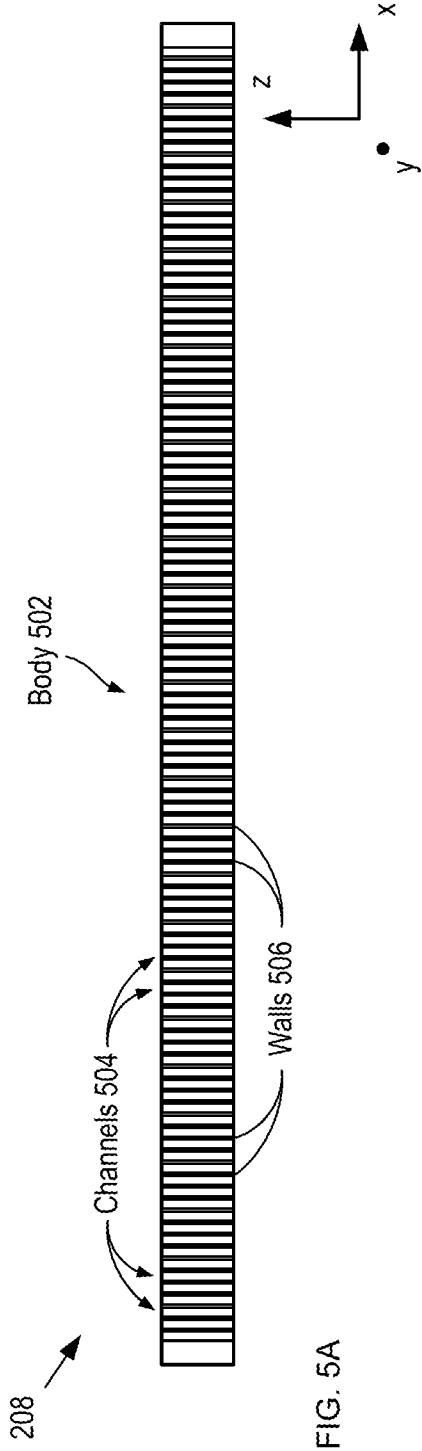


FIG. 4

112 





## INTERNATIONAL SEARCH REPORT

International application No.

PCT/US 2017/033161

A. CLASSIFICATION OF SUBJECT MATTER		<p style="text-align: center;"><i>C23C 14/24 (2006.01)</i> <i>C23C 14/54 (2006.01)</i></p> <p>According to International Patent Classification (IPC) or to both national classification and IPC</p>	
B. FIELDS SEARCHED			
Minimum documentation searched (classification system followed by classification symbols)			
C23C 14/00, 14/06, 14/12, 14/22, 14/24, 14/54			
Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched			
Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)			
Espacenet, PAJ, PatSearch (RUPTO internal), RUPTO, USPTO, WIPO			
C. DOCUMENTS CONSIDERED TO BE RELEVANT			
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.	
X Y A	WO 2000/008228 A1 (CVC, INC.) 17.02.2000, abstract, claims, p.2, 3, lines 1-7, fig.1D	18 1-7, 9-10, 12-14, 16-17, 19-24 8, 11, 15, 25	
Y	US 6287436 B1 (INNOVENT, INC) 11.09.2001, col.4 lines 10-25, 50-67, col.5 lines 1-7, claims, fig.1	1-7, 9-10, 12-14, 16-17, 19-24	
Y	US 7615161 B2 (GENERAL ELECTRIC COMPANY) 10.11.2009, claims, col.6 lines 29-42	4-6, 16, 17, 19-21	
Y	RU 2032765 C1 (FUJITSU LTD) 10.04.1995, p.7 lines 7-49, fig.6-9	7, 9, 13, 23, 24	
Y	RU 2538891 C2 (APPLIED MATERIALS, INC.) 10.01.2015, claims	2-3	
<input checked="" type="checkbox"/> Further documents are listed in the continuation of Box C.		<input type="checkbox"/> See patent family annex.	
* Special categories of cited documents:	“T”	later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention	
“A” document defining the general state of the art which is not considered to be of particular relevance	“X”	document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone	
“E” earlier document but published on or after the international filing date	“Y”	document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art	
“L” document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)	“&”	document member of the same patent family	
“O” document referring to an oral disclosure, use, exhibition or other means			
“P” document published prior to the international filing date but later than the priority date claimed			
Date of the actual completion of the international search	Date of mailing of the international search report		
11 August 2017 (11.08.2017)	24 August 2017 (24.08.2017)		
Name and mailing address of the ISA/RU: Federal Institute of Industrial Property, Berezhkovskaya nab., 30-1, Moscow, G-59, GSP-3, Russia, 125993 Facsimile No: (8-495) 531-63-18, (8-499) 243-33-37	Authorized officer  A. Pimenova  Telephone No. (495) 531 64 81		

## INTERNATIONAL SEARCH REPORT

International application No.

PCT/US 2017/033161

C (Continuation). DOCUMENTS CONSIDERED TO BE RELEVANT		
Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
Y	RU 2014138799 A (OBSHESTVO S OGRANICHENNOY OTVETSTVENNOSTIYU "LASKOM") 20.04.2016, claims	10, 14, 22-24
Y	RU 2155204 C2 (INSTITUT PROBLEM KHIMICHESKOY FIZIKI RAN) 27.08.2000, claims	3